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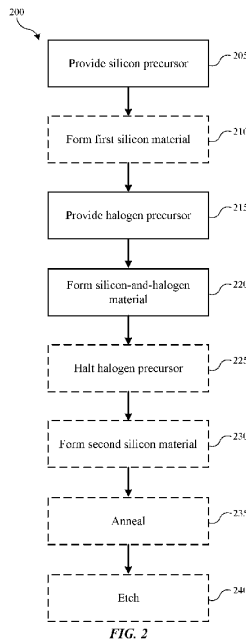
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(54) Title: ELECTRICAL IMPROVEMENTS FOR 3D NAND



(57) Abstract: Exemplary semiconductor processing methods may include providing a silicon-containing precursor to a processing region of a semiconductor processing chamber. A substrate may be disposed within the processing region of the semiconductor processing chamber. Alternating layers of material may be formed on the substrate. One or more recesses may be formed in the alternating layers of material. The methods may include forming a first silicon-containing material. The first silicon-containing material may extend into the one or more recesses formed in the alternating layers of material. The methods may include providing a halogen-containing precursor to the processing region of the semiconductor processing chamber. The methods may include forming a silicon-and-halogen-containing material. The silicon-and-halogen-containing material may overlie the first silicon-containing material. The methods may include forming a second silicon-containing material. The second silicon-containing material may overlie the silicon-and-halogen-containing material.

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